

SILICON SCHOTTKY BARRIER DIODE

DESCRIPTION:

The **ASI BAT39** is a silicon Schottky barrier mixer diode, Designed for use in X frequency band Applications.

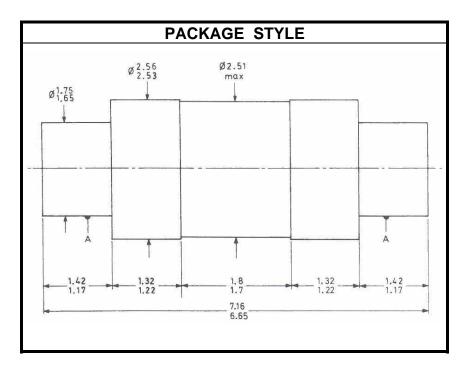
FEATURES INCLUDE:

- \bullet Low R_s–5.0 Ω
- Low NF 6.0 Db Typ.
- Frequency Range 26 to 40 GHz

• Available as Matched pairs by adding the MP to the part number. Matching criteria is \pm 10% on rectified current and within 150 Ω i.f. impedance.

MAXIMUM RATINGS

V _R	2.0 V				
P _{DISS}	250 mW @ T _c = 25 °C				
TJ	-55 °C to +100 °C				
T _{STG}	-55 °C to +100 °C				



CHARACTERISTICS T_c = 25 °C

SYMBOL	TEST CON	DITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
V _R	I _R = 10 μA		2.0			V
V _F	I _F = 1.0 mA				0.29	V
I _F	V _F = 0.5 V			7.0		mA
I _R	V _R = 0.5 V				2.0	μA
CT	V _R = 0 V	f = 1.0 MHz		.27		pF
NF	I _F = 0.5 mA	f = 30 GHz		6.0		dB

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Specifications are subject to change without notice.